PAGE 6/7 * RCVD AT 7/14/2004 11:18:26 AM [Eastern Daylight Time] * SVR:USPTO-EFXRF-1/5 * DNIS:8729306 * CSID:518 449 0047 * DURATION (mm-ss):02-00

Remarks

Claims 1-12 and 21 are pending. By this Amendment, claims 1, 8, and 21 have been

amended. No new matter is believed added.

Claims 1-4, 8, and 21 are rejected under 35 U.S.C. § 102(b) over Merchant (U.S. Patent

No. 5,412,241). Claims 5 and 9 are rejected under 35 U.S.C. § 103(a) over Merchant in view of

Letavic et al. (U.S. Patent No. 6,310,378). Claims 6 and 10 are rejected under 35 U.S.C. §

103(a) over Merchant in view of Seeds et al. (U.S. Patent No. 3,936,858). Claims 7 and 11 are

rejected under 35 U.S.C. § 103(a) over Merchant. Claim 12 is rejected under 35 U.S.C. § 103(a)

over Merchant, Seeds and Shirahata et al. (U.S. Pub. No. 2002/0175380).

Applicants assert that the rejections under 35 U.S.C. § 102(b) are defective because

Merchant fails to teach or suggest each and every feature of the claimed invention as required by

35 U.S.C. §102(b). The remaining references fail to remedy the deficiencies of Merchant.

In the above-referenced Office Action, the Examiner alleges that Merchant discloses the

claimed "second gate oxide formed over a portion of the first gate oxide," and asserts that "(G2)

can be considered the second gate oxide (For Example: See Marked Up Figure 1)."

It should be noted that this rejection is incomplete because a marked up copy of FIG. 1 of

Merchant has not been provided by the Examiner in the above-referenced Office Action.

Further, the reference "G2" does not appear anywhere in FIG. 1 of Merchant. As such, it is not

clear which layer of Merchant is being referred to by the Examiner. Clarification of the rejection

is requested.

It should also be noted that in the Office Actions of December 19, 2002, May 14, 2003,

and November 18, 2003, the Examiner stated that Mcrchant did not disclose the claimed "second

gate oxide." Now, the Examiner alleges that Merchant does indeed disclose this claim feature.

Serial No.: 10/015,847

5 of 6

PAGE 7/7 * RCVD AT 7/14/2004 11:18:26 AM [Eastern Daylight Time] * SVR:USPTO-EFXRF-1/5 * DNIS:8729306 * CSID:518 449 0047 * DURATION (mm-ss):02-09

Applicants respectfully object to this inconsistent analysis of Merchant, and the resultant

unnecessary delay and expense to Applicants.

Regarding independent claim 1, Merchant fails to teach or suggest, among other features,

a "second gate oxide formed over a portion of the first gate oxide that contacts, and is located

directly above, a drift region of the silicon layer." Regarding independent claim 8, Merchant

fails to teach or suggest, among other features, a "second gate oxide formed over a portion of the

first gate oxide that is located between the top oxide layer and the body region, and that contacts,

and is located directly above, the drift region of the silicon layer." Regarding independent claim

21. Merchant fails to teach or suggest, among other features, a "second gate oxide formed over a

portion of the first gate oxide, wherein the second gate oxide and the first gate oxide form a

stepped oxide region that contacts, and is located directly above, the drift region of the silicon

layer." On the contrary, Merchant discloses a structure similar to that depicted in the related art

FIGS. 1 and 2 of the present patent application.

In light of the above, Applicants submit that all pending claims are in condition for

allowance. If the Examiner believes that anything further is necessary to place the application in

condition for allowance, the Examiner is requested to contact Applicants' undersigned attorney

at the telephone number listed below.

Respectfully submitted,

Dated: 7/14/04

Hoffman, Warnick & D'Alessandro LLC

Three E-Comm Square

Albany, NY 12207

(518) 449-0044 - Telephone

(518) 449-0047 - Facsimile

Reg. No. 35,812

Serial No.: 10/015,847

6 of 6